



**DIODES, MICROWAVE, SILICON,
PIN, FAST SWITCHING,
BASED ON TYPES ML4603-54 THRU ML4608-54
ESCC Detail Specification No. 5513/004**

**ISSUE 1
October 2002**



	ESCC Detail Specification		PAGE ii ISSUE 1
---	---------------------------	--	--------------------

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2002. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole in any medium without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



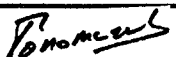

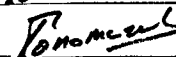
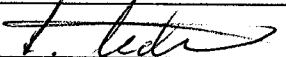
europaean space agency
agence spatiale européenne

Pages 1 to 19

**DIODES, MICROWAVE, SILICON,
PIN, FAST SWITCHING,
BASED ON TYPES ML4603-54 THRU ML4608-54
ESA/SCC Detail Specification No. 5513/004**



**space components
coordination group**

Issue/Rev.	Date	Approved by	
		SCCG Chairman	ESA Director General or his Deputy
Issue 1	November 1992		
Revision 'A'	December 1993		

**SCC**ESA/SCC Detail Specification
No. 5513/004

Rev. 'A'

PAGE 2

ISSUE 1

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
'A'	Dec '93	P1. Cover Page P2. DCN P4. T of C P12. Table 2 P13. Table 3 Table 4 P17. Table 6	: 'Type Variant' changed to 'Type Variants' : Table standardised : Table standardised : Table standardised : Table standardised	None None 23619 23619 23619 23619 23619




 SCC	ESA/SCC Detail Specification No. 5513/004		PAGE 3 ISSUE 1
--	--	--	-------------------

TABLE OF CONTENTS



	<u>Page</u>
1. GENERAL	5
1.1 Scope	5
1.2 Type Variants	5
1.3 Maximum Ratings	5
1.4 Parameter Derating Information	5
1.5 Physical Dimensions	5
1.6 Functional Diagram	5
1.7 Handling Precautions	5
2. APPLICABLE DOCUMENTS	5
3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	5
4. REQUIREMENTS	9
4.1 General	9
4.2 Deviations from Generic Specification	9
4.2.1 Deviations from Special In-process Controls	9
4.2.2 Deviations from Final Production Tests	9
4.2.3 Deviations from Burn-in and Electrical Measurements	9
4.2.4 Deviations from Qualification Tests	9
4.2.5 Deviations from Lot Acceptance Tests	9
4.3 Mechanical and Environmental Requirements	9
4.3.1 Dimension Check	9
4.3.2 Weight	9
4.3.3 Terminal Strength	10
4.4 Materials and Finishes	10
4.4.1 Case	10
4.4.2 Lead Materials and Finish	10
4.5 Marking	10
4.5.1 General	10
4.5.2 Cathode Identification	10
4.5.3 The SCC Component Number	10
4.5.4 Traceability Information	11
4.6 Electrical Measurements	11
4.6.1 Electrical Measurements at Room Temperature	11
4.6.2 Electrical Measurements at High and Low Temperatures	11
4.6.3 Circuits for Electrical Measurements	11
4.7 Burn-in Tests	11
4.7.1 Parameter Drift Values	11
4.7.2 Conditions for High Temperature Reverse Bias Burn-in	11
4.7.3 Conditions for Power Burn-in	11
4.7.4 Electrical Circuits for High Temperature Reverse Bias and Power Burn-in	11
4.8 Environmental and Endurance Tests	16
4.8.1 Electrical Measurements on Completion of Environmental Tests	16
4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests	16
4.8.3 Conditions for Operating Life Tests	16
4.8.4 Electrical Circuits for Operating Life Tests	16
4.9 Total Dose Irradiation Testing	16
4.9.1 Application	16
4.9.2 Bias Conditions	16
4.9.3 Electrical Measurements	16
4.10 Special Testing	16

		<p style="text-align: center;">ESA/SCC Detail Specification No. 5513/004</p>	<p style="text-align: center;">Rev. 'A'</p>	<p>PAGE 4 ISSUE 1</p>
---	---	--	---	---------------------------

<u>TABLES</u>	<u>Page</u>
1(a) Type Variants	6
1(b) Maximum Ratings	6
2 Electrical Measurements at Room Temperature - D.C. Parameters	12
Electrical Measurements at Room Temperature - A.C. Parameters	12
3 Electrical Measurements at High and Low Temperatures	13
4 Parameter Drift Values	13
5(a) Conditions for High Temperature Reverse Bias Burn-in	15
5(b) Conditions for Power Burn-in	15
5(c) Conditions for Operating Life Tests	15
6 Electrical Measurements at Intermediate Points and on Completion of Endurance Testing	17
7 Electrical Measurements During and on Completion of Irradiation Testing	18

<u>FIGURES</u>	
1 Parameter Derating Information	7
2 Physical Dimensions	8
3 Functional Diagram	8
4 Circuits for Electrical Measurements	14
5(a) Electrical Circuit for High Temperature Reverse Bias Burn-in	15
5(b) Electrical Circuit for Power Burn-in and Operating Life Tests	15
6 Bias Conditions for Irradiation Testing	17

<u>APPENDICES (Applicable to specific Manufacturers only)</u>	
'A' Agreed deviations for M/A-Com Ltd. (G.B.)	19

		<p style="text-align: center;">ESA/SCC Detail Specification No. 5513/004</p>		<p>PAGE 5 ISSUE 1</p>
---	---	--	--	---------------------------

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Diode, Microwave, Silicon, PIN, Fast Switching, based on Types ML4603-54 thru ML4608-54. It shall be read in conjunction with ESA/SCC Generic Specification No. 5010, the requirements of which are supplemented herein.

1.2 TYPE VARIANTS

Variants of the basic diodes specified herein, which are also covered by this specification are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the diodes specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

1.7 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are Categorised as Class 1 with a Minimum Critical Path Failure Voltage of 1000V.

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESA/SCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

**TABLE 1(a) - TYPE VARIANTS**

(1) VARIANT	(2) BASED ON TYPE	(3) FIGURE	(4) TOTAL CAPACITANCE C_T (pF)		(5) JUNCTION CAPACITANCE C_J (pF) (Typical)	(6) LEAD MATERIAL AND FINISH
			MIN	MAX		
01	ML4603 - 54	2	0.10	0.20	0.10	C4
02	ML4604 - 54	2	0.30	0.40	0.30	C4
03	ML4605 - 54	2	1.00	1.20	1.05	C4
04	ML4606 - 54	2	0.10	0.20	0.10	C4
05	ML4607 - 54	2	0.30	0.40	0.30	C4
06	ML4608 - 54	2	0.95	1.15	1.05	C4

TABLE 1(b) - MAXIMUM RATINGS

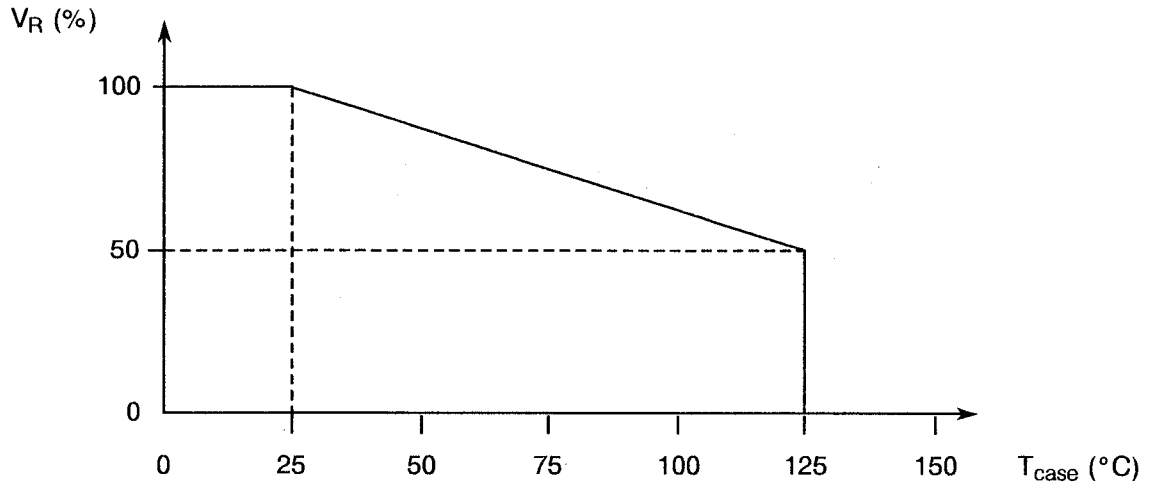
No.	CHARACTERISTIC	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	D.C. Reverse Voltage Variants 01 to 03 Variants 04 to 06	V_R	- 35 - 100	V	Note 1
2	D.C. Forward Current (Continuous)	I_F	100	mA	Note 1
3	R.F. Power Dissipation	P_{tot}	200	mW	Note 1
4	Operating Temperature Range	T_{op}	- 65 to +125	°C	T_{case}
5	Storage Temperature Range	T_{stg}	- 65 to +125	°C	
6	Soldering Temperature	T_{sol}	+ 230	°C	Note 2

NOTES

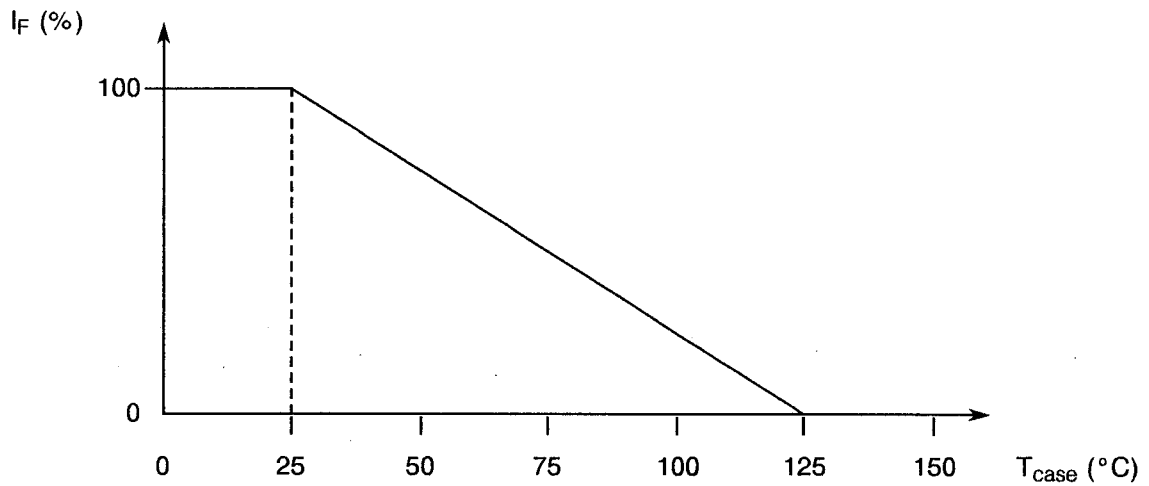
1. At $T_{case} = +25^\circ\text{C}$. For derating at $T_{case} > +25^\circ\text{C}$, see Figure 1.
2. Duration 5 seconds maximum at a distance of not less than 1.5mm from the body and the same termination shall not be resoldered until 3 minutes have elapsed.



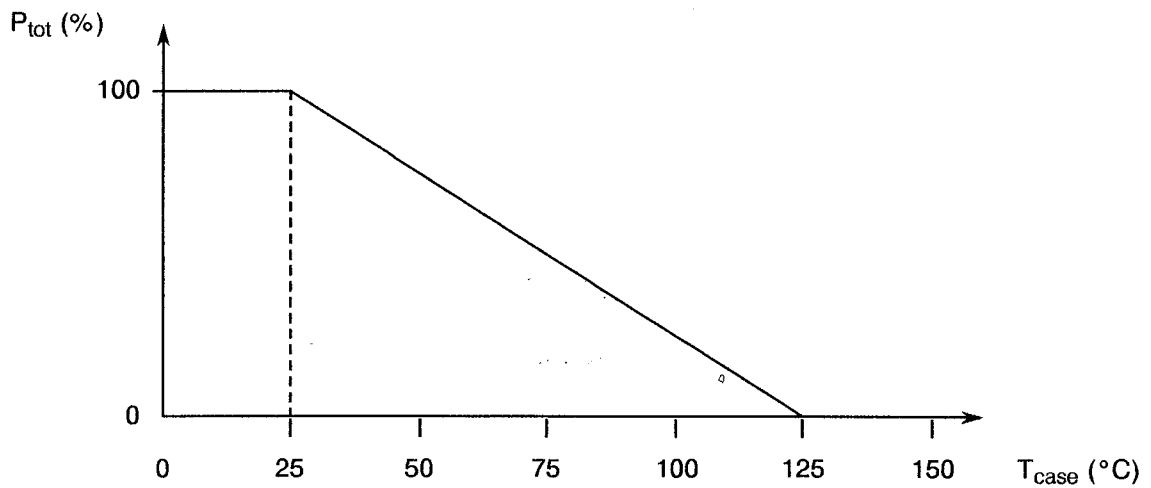
FIGURE 1 - PARAMETER DERATING INFORMATION



Reverse Voltage versus Temperature



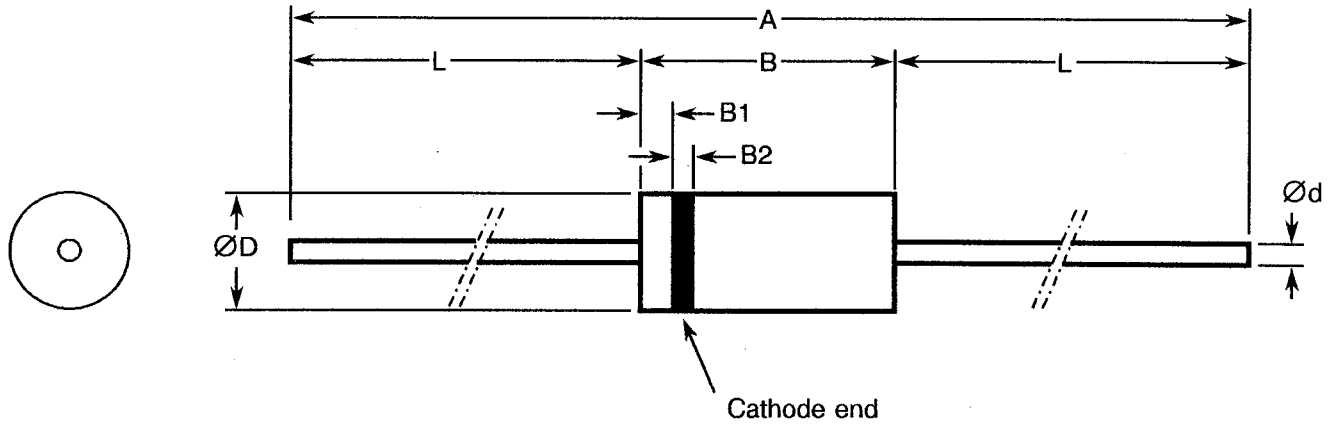
Forward Current versus Temperature



Power Dissipation versus Temperature



FIGURE 2 - PHYSICAL DIMENSIONS



SYMBOL	MILLIMETRES	
	MIN	MAX
A	54.48	80.39
B	3.68	4.19
B1	0.10	1.04
B2	0.30	0.80
Ød	0.35	0.41
ØD	1.73	1.91
L	25.40	38.10

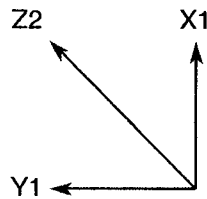
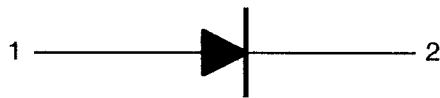



FIGURE 3 - FUNCTIONAL DIAGRAM



- 1. Anode
- 2. Cathode

NOTES

- 1. The cathode end shall be marked with a black band.

	<p style="text-align: center;">ESA/SCC Detail Specification No. 5513/004</p>	<p>PAGE 9 ISSUE 1</p>
---	--	---------------------------

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the diodes specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 5010 for Discrete Microwave Semiconductor Components. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

- (a) Para. 5.2.2, Total Dose Irradiation Testing: Shall be performed during qualification and extension of qualification.
- (b) Para. 5.2.2, Total Dose Irradiation Testing: Shall be performed during procurement on a lot acceptance basis at the total dose irradiation level specified in the purchase order.
- (c) Para. 5.3, Wafer Lot Acceptance: Shall be performed as an S.E.M. Inspection only.

4.2.2 Deviations from Final Production Tests (Chart II)

- (a) Para. 6.2, Pre-burn-in: Shall be performed in accordance with Para. 9.21(a).
- (b) Para. 9.2.1, Bond Strength: Shall not be performed.
- (c) Para. 9.2.2, Die Shear: Shall not be performed and no additional thermal tests shall be performed to replace this test.
- (d) Para. 9.14, Vibration, Variable Frequency: Shall not be performed.

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) Para. 7.1.1(a), High Temperature Reverse Bias Burn-in: Shall be performed at 50% of rated V_R .

4.2.4 Deviations from Qualification Tests (Chart IV)

- (a) Para. 9.2.3, Bond Strength: Shall not be performed.
- (b) Para. 9.2.4, Die Shear: Shall not be performed. Thermal resistance measurements shall be performed in accordance with Table 2 of this specification.
- (c) Para. 9.23, Special Testing: Shall not be performed.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

- (a) Para. 9.23, Special Testing: Shall not be performed.

4.3 MECHANICAL AND ENVIRONMENTAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the diodes specified herein shall be 0.10 grammes.

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5010. The test conditions shall be as follows:-

- (a) Condition: 'A' (Tension).
- (b) Force: 5.0N.
- (c) Duration: 5 seconds.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material shall not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a glass body.

4.4.2 Lead Materials and Finish

The material shall be Type 'C' with Type '4' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.

4.5 MARKING

4.5.1 General

The marking of components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700 and the following paragraphs. When the component is too small to accommodate all of the marking specified, as much as space permits shall be marked and the marking information, in full, shall accompany the component in its primary package.

The information to be marked and the order of precedence, shall be as follows:-

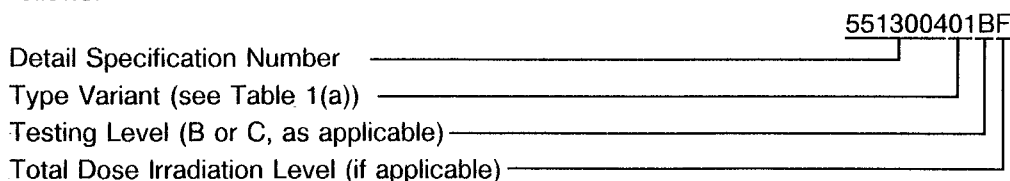
- (a) Cathode Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Cathode Identification


Cathode identification shall be as shown in Figures 2 and 3 of this specification.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:



The Total Dose Irradiation Level designation shall be added for those devices for which a sample has been successfully tested to the level in question. For these devices, a code letter shall be added in accordance with the requirements of ESA/SCC Basic Specification No. 22900.

	ESA/SCC Detail Specification No. 5513/004		PAGE 11 ISSUE 1
---	--	--	--------------------

4.5.4 Traceability Information

Each component shall be marked in respect of traceability information as defined in ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. Unless otherwise specified, the measurements shall be performed at $+125(+0-3)$ °C.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing electrical measurements listed in Table 2 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

Burn-in shall be Category 3 of Chart III(a).

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the scheduled parameters shall not be exceeded. In addition to these drift value requirements for a given parameter, the appropriate limit value specified in Table 2 shall not be exceeded.

4.7.2 Conditions for High Temperature Reverse Bias Burn-in

The requirements for the high temperature reverse bias burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5010. The conditions for high temperature reverse bias burn-in shall be as specified in Table 5(a) of this specification.

4.7.3 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5010. The conditions for power burn-in shall be as specified in Table 5(b) of this specification.

4.7.4 Electrical Circuits for High Temperature Reverse Bias and Power Burn-in

Circuits for use in performing the H.T.R.B and power burn-in tests are shown in Figures 5(a) and 5(b) of this specification.

**SCC**ESA/SCC Detail Specification
No. 5513/004

Rev. 'A'

PAGE 12

ISSUE 1

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - D.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current 1	I_{R1}	4016	Variants 01 to 03 $V_R = -35V$ Variants 04 to 06 $V_R = -100V$	-	10	μA
2	Reverse Current 2	I_{R2}	4016	Variants 01 to 03 $V_R = -17.5V$ Variants 04 to 06 $V_R = -50V$	-	50	nA
3	Forward Voltage	V_F	4011	$I_F = 100mA$	-	1.0	V
4	Thermal Resistance	$R_{TH(J-C)}$	3101	$I_F = 1.0A$ Note 1	-	500	$^{\circ}C/W$

NOTES

1. Pulsed measurement, pulse width = 4.0 μs , p.r.f. = 1.0kHz.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - A.C. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST FIG.	TEST CONDITIONS	LIMITS		UNIT
						MIN.	MAX.	
5	Total Capacitance	C_T	4001	-	$V_R = -10V$ $f = 1.0MHz$	Note 1		pF
6	Minority Carrier Lifetime	τ_L	-	4(a)	Variants 01 to 03 $I_F = 10mA$	-	300	ns
					Variants 04 to 06 $I_F = 4.5mA$	-	700	
7	Forward Slope Resistance	R_{FS}	-	4(b)	$I_F = 40mA$ $f_o = 500MHz$			Ω
					Variants 01 and 04	-	1.7	
					Variants 02 and 05	-	1.0	
					Variants 03 and 06	-	0.8	

NOTES

1. See Column 4 of Table 1(a).

**TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES**

No.	CHARACTERISTICS	SYMBOL	SPEC.AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	-	10	μA

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC.AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	± 10 (1) or (2) ± 100 (1)	nA %
3	Forward Voltage	V_F	As per Table 2	As per Table 2	± 100 (1)	mV

NOTES

1. $\Delta 1 = \Delta 2 = \Delta 3$
2. Whichever is the greater, referred to the initial measurement.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - MINORITY CARRIER LIFETIME

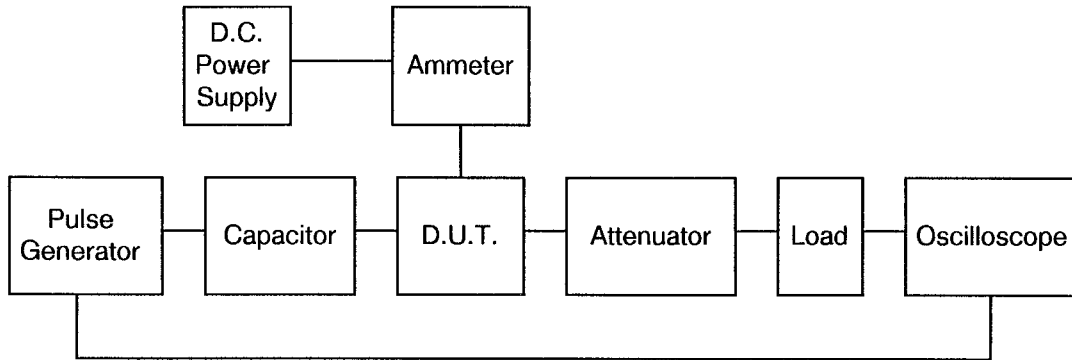


FIGURE 4(b) - FORWARD SLOPE RESISTANCE

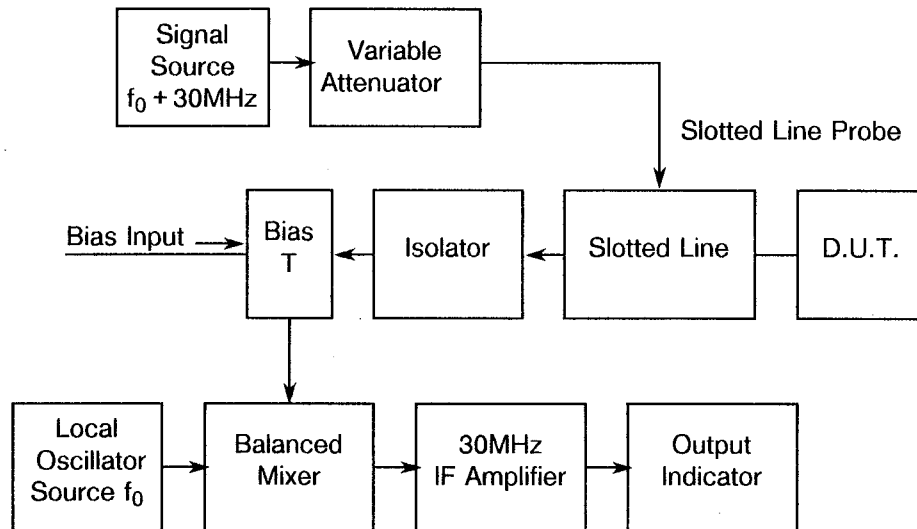


TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T_{amb}	$+ 125(+ 0 - 3)$	$^{\circ}C$
2	Reverse Voltage	V_R	Variants 01 to 03 $- 17.5$ Variants 04 to 06 $- 50$	V

TABLE 5(b) - CONDITIONS FOR POWER BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T_{amb}	$+ 115(+ 0 - 3)$	$^{\circ}C$
2	Forward Current	I_F	10	mA

TABLE 5(c) - CONDITIONS FOR OPERATING LIFE TESTS

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature 1	T_{amb1}	$+ 105(+ 0 - 3)$	$^{\circ}C$
2	Forward Current 1	I_{F1}	10	mA
3	Ambient Temperature 2	T_{amb2}	$+ 115(+ 0 - 3)$	$^{\circ}C$
4	Forward Current 2	I_{F2}	10	mA

FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

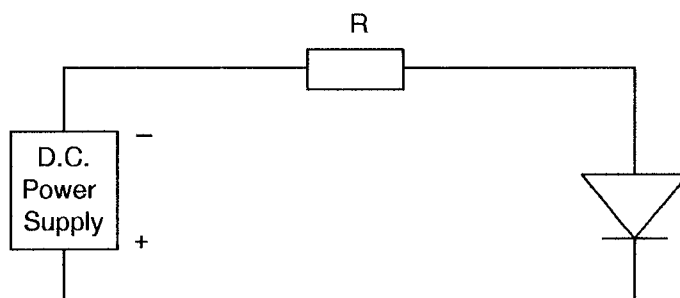
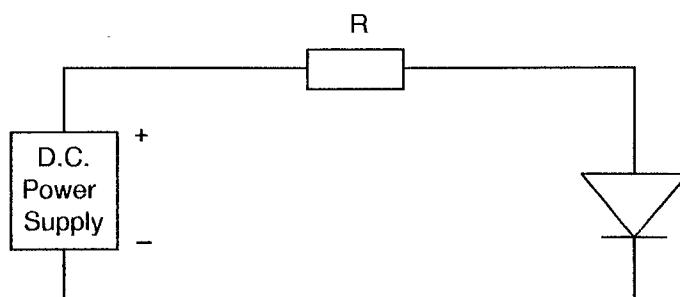



FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TESTS



	<p style="text-align: center;">ESA/SCC Detail Specification No. 5513/004</p>	<p style="text-align: right;">PAGE 16 ISSUE 1</p>
---	--	---

4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 5010)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests

The parameters to be measured at intermediate points and on completion of endurance tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5010. The conditions for operating life testing are specified in Table 5(c) of this specification.

4.8.4 Electrical Circuits for Operating Life Tests

The circuit to be used for performance of the operating life test shall be the same as shown in Figure 5(b) for Power Burn-in.

4.9 TOTAL DOSE IRRADIATION TESTING

4.9.1 Application

If specified in Para. 4.2.1 of this specification, total dose irradiation testing shall be performed in accordance with the requirements of ESA/SCC Basic Specification No. 22900.

4.9.2 Bias Conditions

Continuous bias shall be applied during irradiation testing as shown in Figure 6 of this specification.

4.9.3 Electrical Measurements

The parameters to be measured prior to irradiation exposure are scheduled in Table 2 of this specification. Only devices which meet the requirements of Table 2 shall be included in the test sample.

The parameters to be measured during and on completion of irradiation testing are scheduled in Table 7 of this specification.

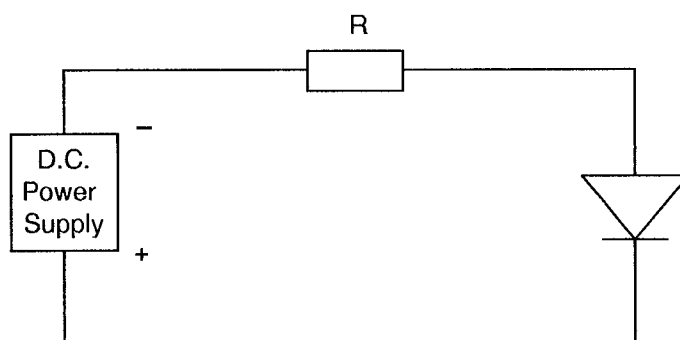
4.10 SPECIAL TESTING

Not applicable.

TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current 1	I_{R1}	As per Table 2	As per Table 2	As per Table 2		μA
2	Reverse Current 2	I_{R2}	As per Table 2	As per Table 2	As per Table 2		nA
3	Forward Voltage	V_F	As per Table 2	As per Table 2	As per Table 2		V
5	Total Capacitance	C_T	As per Table 2	As per Table 2	As per Table 2		pF
7	Forward Slope Resistance	R_{FS}	As per Table 2	As per Table 2	As per Table 2		Ω

FIGURE 6 - BIAS CONDITIONS FOR IRRADIATION TESTING



NOTES

1. A reverse bias shall be applied as follows:
 - Variants 01 to 03 : $V_R = -17.5V$.
 - Variants 04 to 06 : $V_R = -50V$.

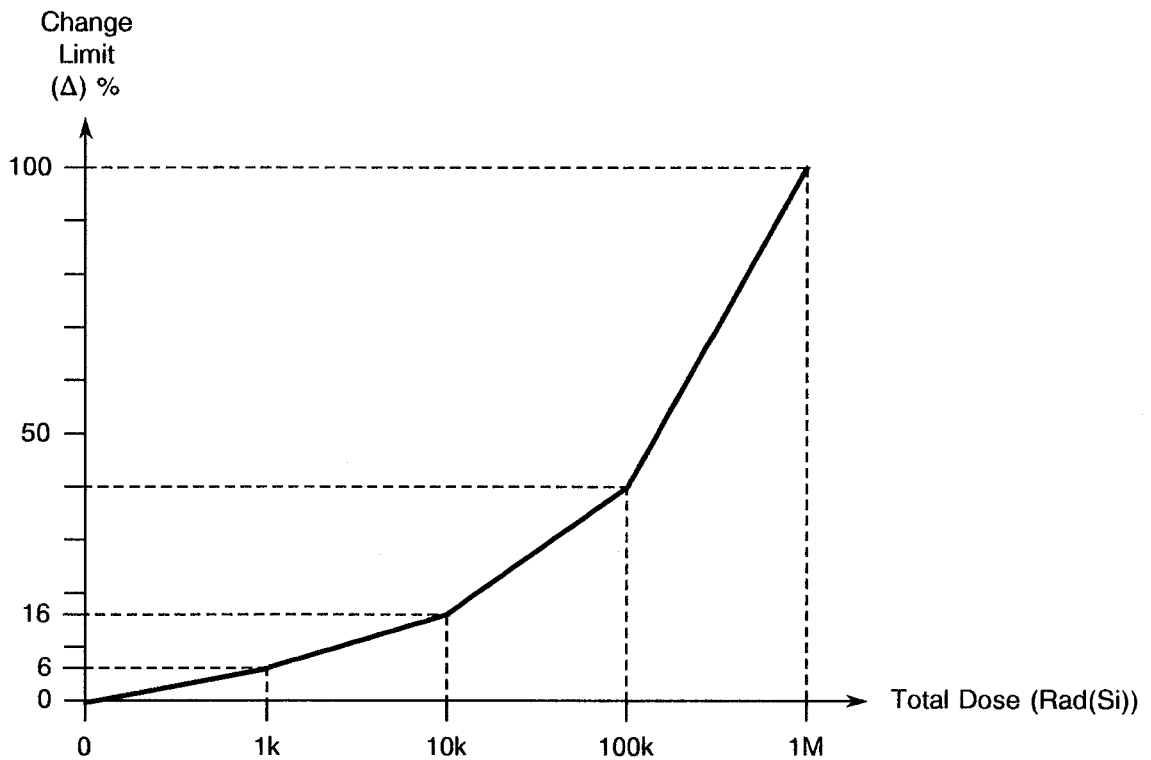



TABLE 7 - ELECTRICAL MEASUREMENTS DURING AND ON COMPLETION OF IRRADIATION TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
6	Minority Carrier Lifetime	τ_L	As per Table 2	As per Table 2	Note 1	%

NOTES

1. The graph given below shall be used to determine the maximum permitted change.



	<p>ESA/SCC Detail Specification No. 5513/004</p>		<p>PAGE 19 ISSUE 1</p>
---	--	--	----------------------------

APPENDIX 'A'

Page 1 of 1

AGREED DEVIATIONS FOR M/A-Com LTD. (G.B.)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 4.2.2	Para. 9.4, "High Temperature Stabilisation Bake": May be performed at +125(+0-3) °C.